



NPN TRANSISTOR

FEATURES

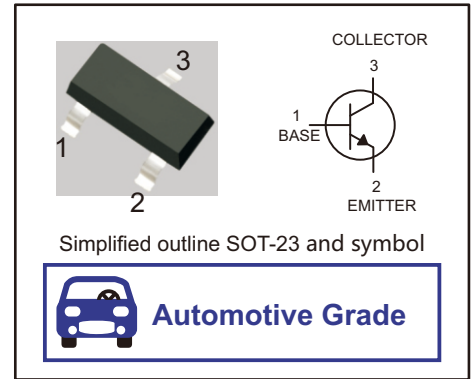
- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- We declare that the material of product compliance with RoHS requirements
- Qualified to AEC-Q101 Standards for High Reliability

APPLICATIONS

- Supply line switching circuits
- Battery management applications
- DC/DC converter applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers)

PINNING

PIN	DESCRIPTION
1	BASE
2	EMITTER
3	COLLECTOR



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector–Base Voltage	V_{CBO}	40	V
Collector–Emitter Voltage	V_{CEO}	40	V
Emitter–Base Voltage	V_{EBO}	5.0	V
Collector Current — Continuous	I_C	2	A
Collector Power Dissipation	P_C	300	mW
Junction temperature	T_J	150	°C
Storage Temperature	T_{stg}	-65~+150	°C

THERMAL CHARACTERISTICS

Symbol	Parameter	Conditions	Value	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air;note 1	417	K/W
		in free air;note 2	260	K/W

Notes:

- 1.Device mounted on a printed-circuit board,single sided copper,tinplated and standard footprint.
- 2.Device mounted on a printed-circuit board,single sided copper,tinplated and mounted pad for collector 1 cm.



ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min	Max	Typ	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{ mA}, I_B = 0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	5.0			V
Collector cut-off current	I_{CBO}	$V_{CB} = 30V, I_E = 0$		100		nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4V, I_C = 0$		100		nA
DC current gain	h_{FE}	$V_{CE} = 2V, I_C = 100\text{mA}$	350			
		$V_{CE} = 2V, I_C = 500\text{mA}$	300			
		$V_{CE} = 2V, I_C = 1A$	300			
		$V_{CE} = 2V, I_C = 2A$	150			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100\text{mA}, I_B = 1\text{mA}$		70		mV
		$I_C = 500\text{mA}, I_B = 50\text{mA}$		100		mV
		$I_C = 750\text{mA}, I_B = 15\text{mA}$		180		mV
		$I_C = 1A, I_B = 50\text{mA}, \text{note 1}$		180		mV
		$I_C = 2A, I_B = 200\text{mA}, \text{note 1}$		320		mV
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 2A, I_B = 200\text{mA}, \text{note 1}$		1.1		V
base-emitter turn on voltage	$V_{BE(on)}$	$I_C = 100\text{mA}, V_{CE} = 2V$		0.75		V
collector capacitance	C_C	$I_E = I_C = 0, V_{CB} = 10V, f = 1\text{MHz}$		20		pF
Transition frequency	f_T	$V_{CE} = 10V, I_C = 100\text{mA}, f = 100\text{MHz}$	100			MHz

Note1: Pulse test: $t_p \leq 300\mu s$, $\delta \leq 0.02$



TYPICAL CHARACTERISTICS

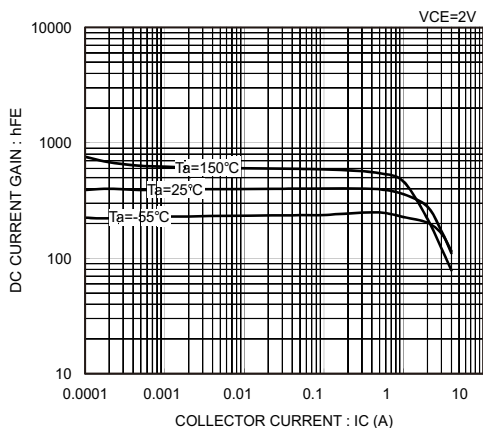


Fig.1 DC CURRENT GAIN VS.COLLECTOR CURRENT

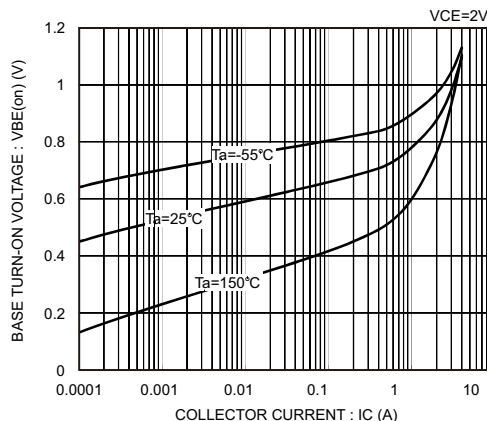


Fig.2 BASE-EMITTER TURN-ON VOLTAGE VS.COLLECTOR CURRENT

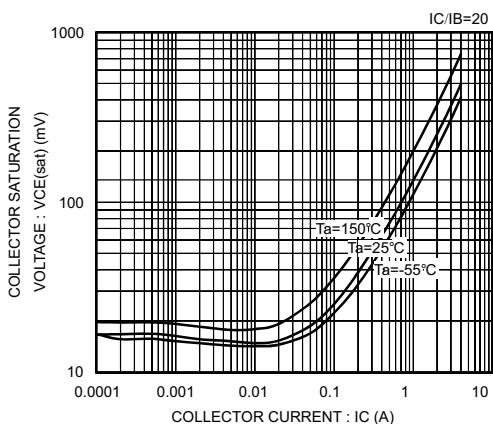


Fig.3 COLLECTOR-EMITTER SATURATION VOLTAGE VS.COLLECTOR CURRENT

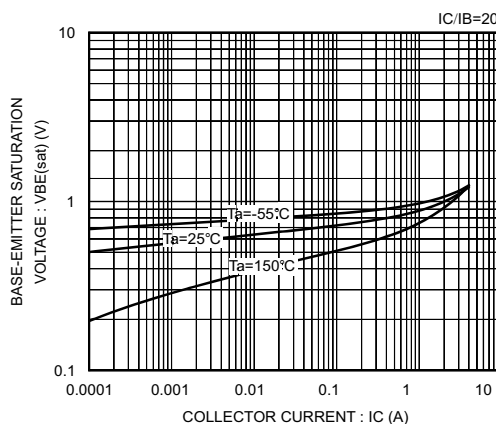


Fig.4 BASE-EMITTER SATURATION VOLTAGE VS.COLLECTOR CURRENT

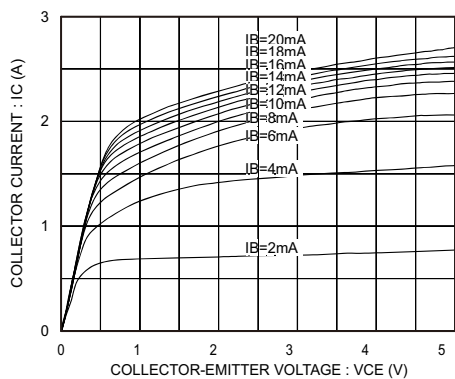


Fig.5 COLLECTOR CURRENT VS.COLLECTOR-EMITTER SATURATION VOLTAGE

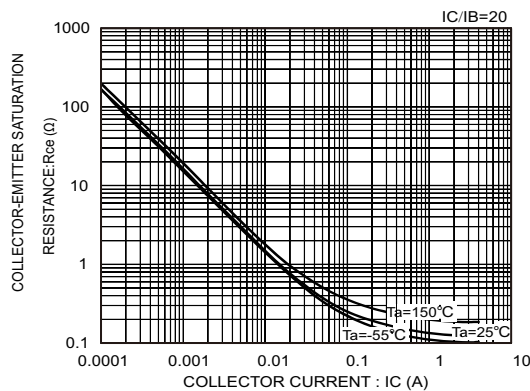
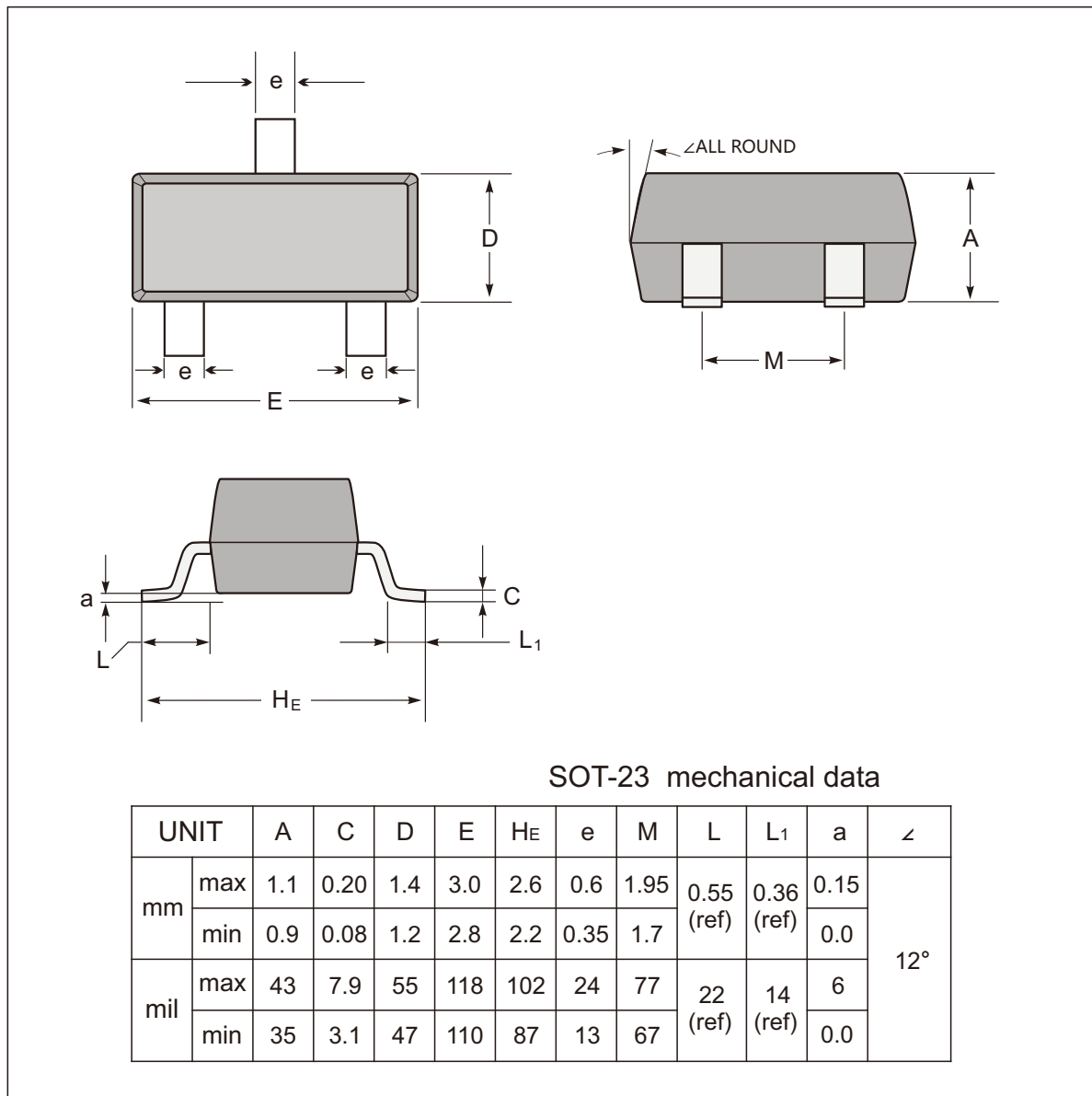


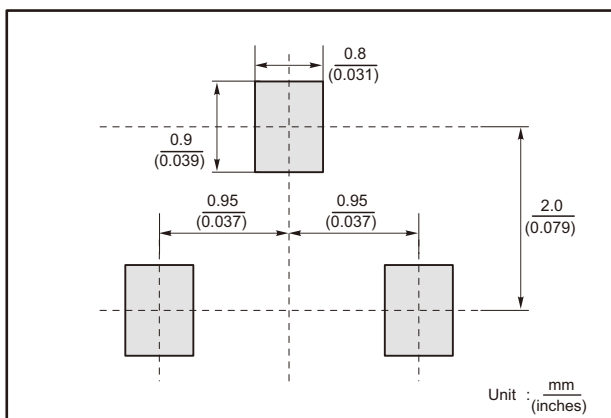
Fig.6 COLLECTOR-EMITTER SATURATION RESISTANCE VS.COLLECTOR CURRENT



SOT-23 Package Outline Dimensions



The recommended mounting pad size



Marking

Type number	Marking code
MMBT4240WD	ZE



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